FOR HIGH SPEED SWITCHING APPLICATION SILICON EPITAXIAL TYPE(CATHODE COMMON, ANODE COMMON)

DESCRIPTION

RT3DKAM is a super mini package plastic seal type silicon epitaxial type composite diode, built with Anode common MC2836 and Cathode common MC2838.

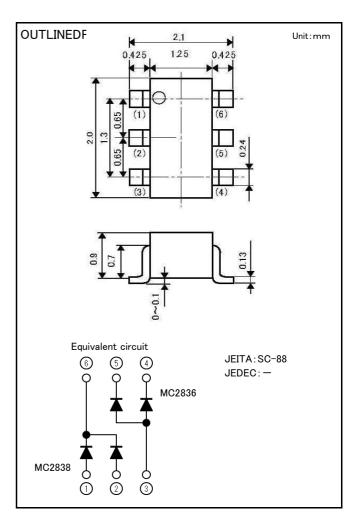
Due to the small pin capacitance, short switching time(reverse recovery time), It is most suitable for high speed switching application and limitter, clipper application.

FEATURE

- Small pin capacitance
- Quick switching time
- ●High voltage
- •Quadruple diodes and super mini package for mounting

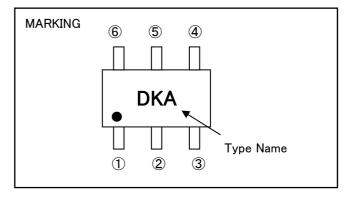
APPLICATION

For general high speed switching of audio machine, VCR.



MAXIMUM RATINGS(Ta=25°C)

Symbol	Parameter	Ratings	Unit	
V _{RM}	Peak reverse voltage	85	V	
V _R	DC reverse voltage	80	V	
I _{FSM}	Surge current(1 μ s)	4	А	
I _{fm}	Peak forward current	300	mA	
Ιo	Average rectification current	100	mA	
P _T	Total allowance dissipation(Ta=25°C)	200	mW	
Tj	Junction temperature	+150	°C	
Tstg	Storage temperature	-55 ~ +150	°C	



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ELECTRICAL CHARACTERISTICS MC2836 (Ta=25°C)

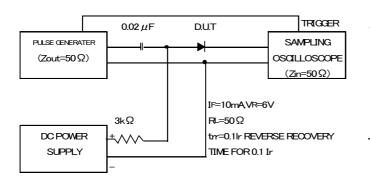
Parameter	Symbol	Test conditions	Limits			Uniit
Parameter			Min	Тур	Max	Unlit
	V_{F1}	I _F =10mA	-	0.77	0.9	
Forward voltage	V_{F2}	I _F =50mA	1	090	1.0	V
	V_{F3}	I _F =100mA	-	0.95	1.2	
Reverse current	I_{R1}	V _R =75V	-	-	0.1	μA
Reverse current	I _{R2}	V _R =80V	-	-	0.5	
Pin capacitance	C _t	V _R =0V, f=1MHz	-	2.8	4.0	pF
Reverse recovery time	trr	(Refer to test circuit)	_	_	4.0	ns

ELECTRICAL CHARACTERISTICS MC2838 (Ta=25°C)

Parameter	Symbol	Test conditions	Limits			Uniit
Parameter			Min	Тур	Max	Unlit
	V_{F1}	I _F =10mA	-	0.72	0.9	
Forward voltage	V_{F2}	I _F =50mA	-	085	1.0	V
	V_{F3}	I _F =100mA	-	0.90	1.2	
Reverse current	I _{R1}	V _R =75V	-	-	0.1	μA
Reverse current	I_{R2}	V _R =80V	-	-	0.5	
Pin capacitance	C _t	V _R =0V, f=1MHz	-	1.3	4.0	pF
Reverse recovery time	trr	(Refer to test circuit)	_	_	3.0	ns

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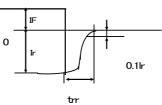
MC2836 Reverse recovery time (trr) test circuit



● INPUT VOLTAGE WAVE FORM



CURRENT WAVE FORM IN DIODE



MC2836 TYPACAL CHARACTERISTICS

5

2

1

0.5

0.2

0.1

2

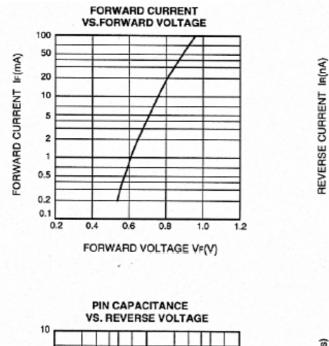
5

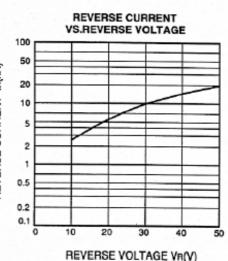
10 20

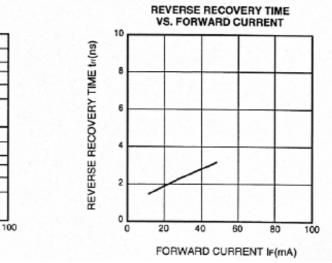
REVERSE VOLTAGE VR(V)

50

PIN CAPACITANCE CI(pF)

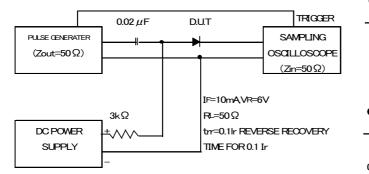




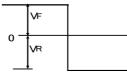


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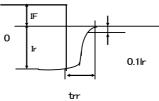
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● INPUT VOLTAGE WAVE FORM

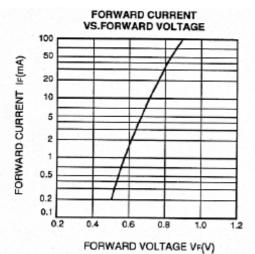


CURRENT WAVE FORM IN DIODE



MC2838 TYPACAL CHARACTERISTICS

MC2838 Reverse recovery time (trr) test circuit



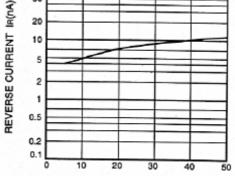
VS.REVERSE VOLTAGE

100

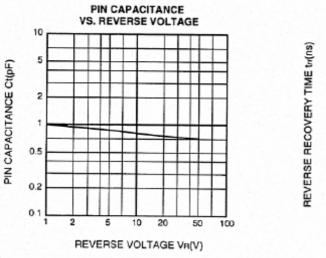
50

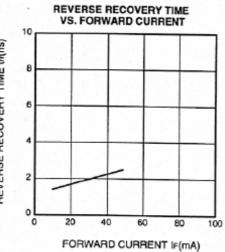
20

REVERSE CURRENT



REVERSE VOLTAGE VR(V)





ISAHAYA ELECTRONICS CORPORATION



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